

FIG. 1

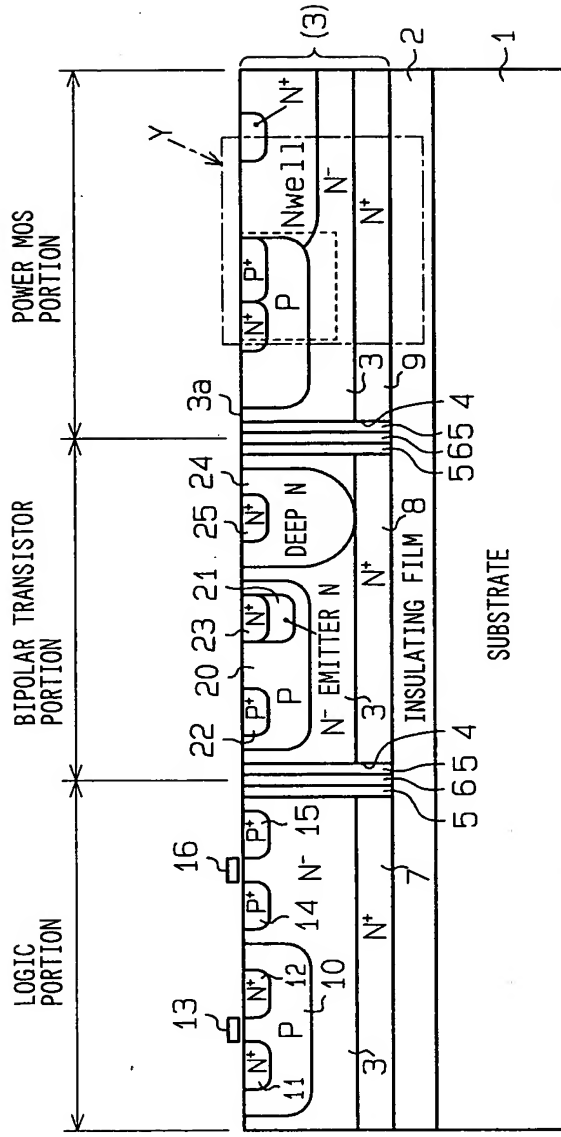


FIG. 2

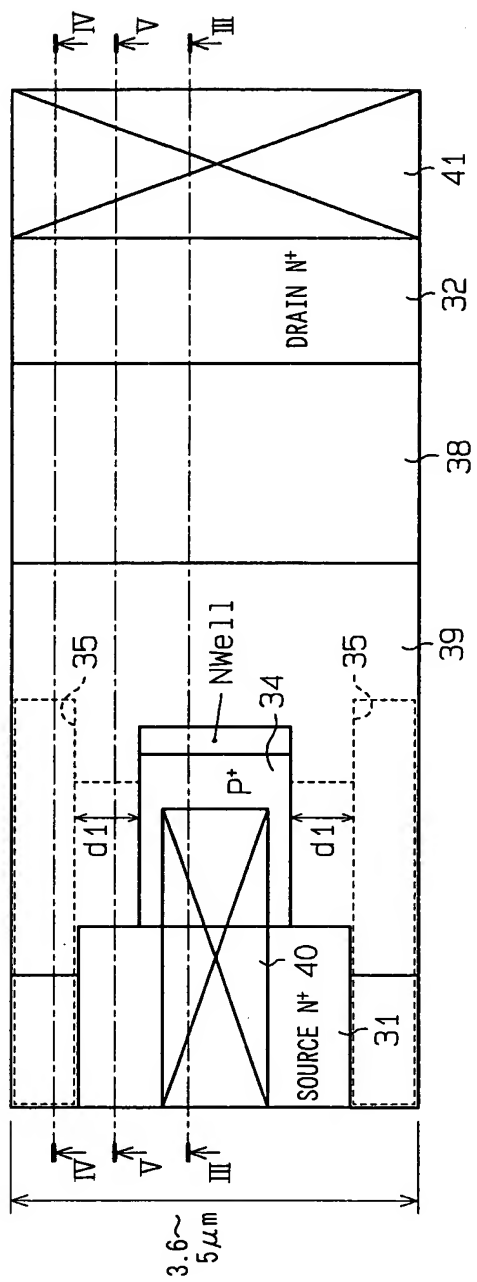


FIG. 3

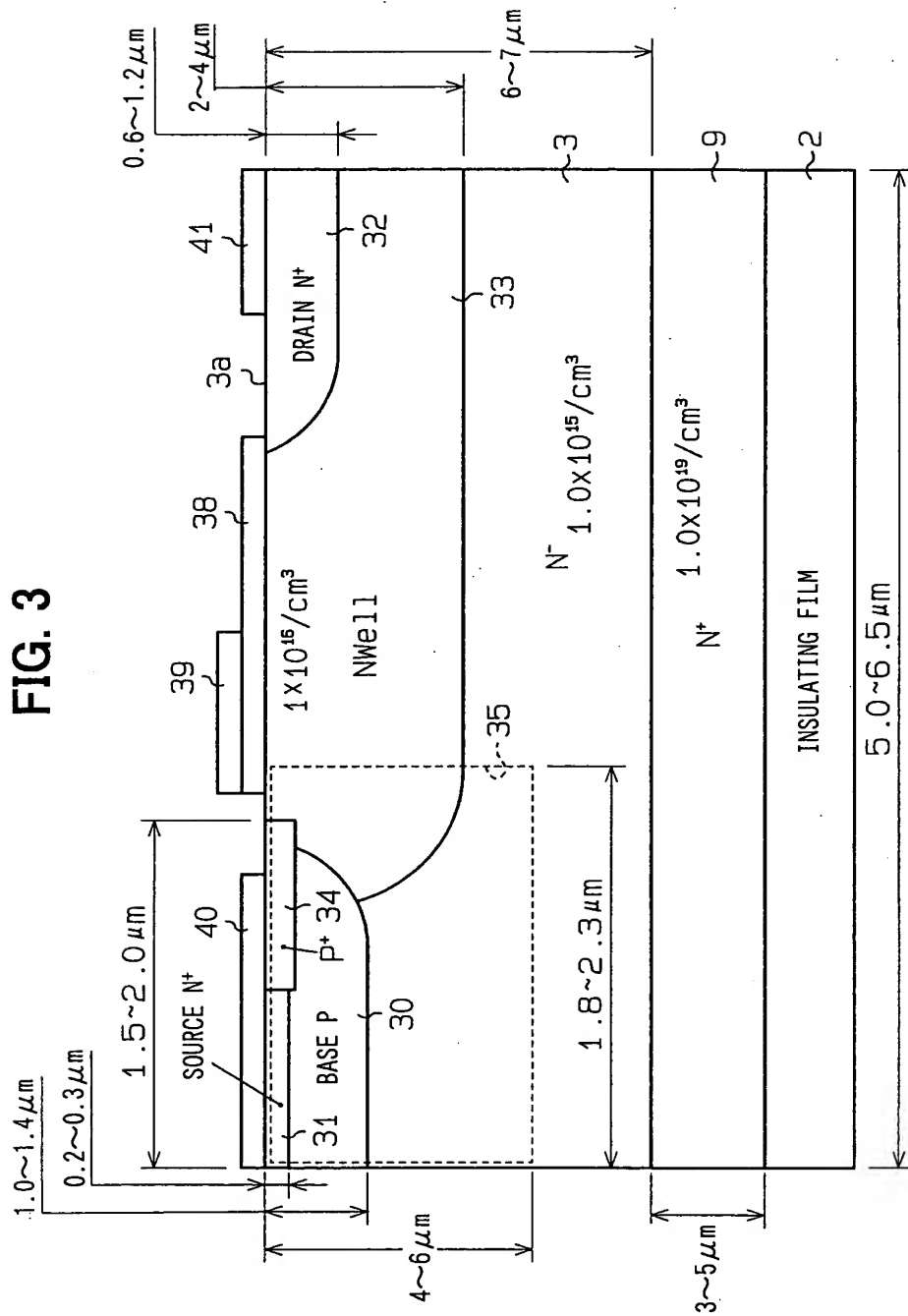


FIG. 4

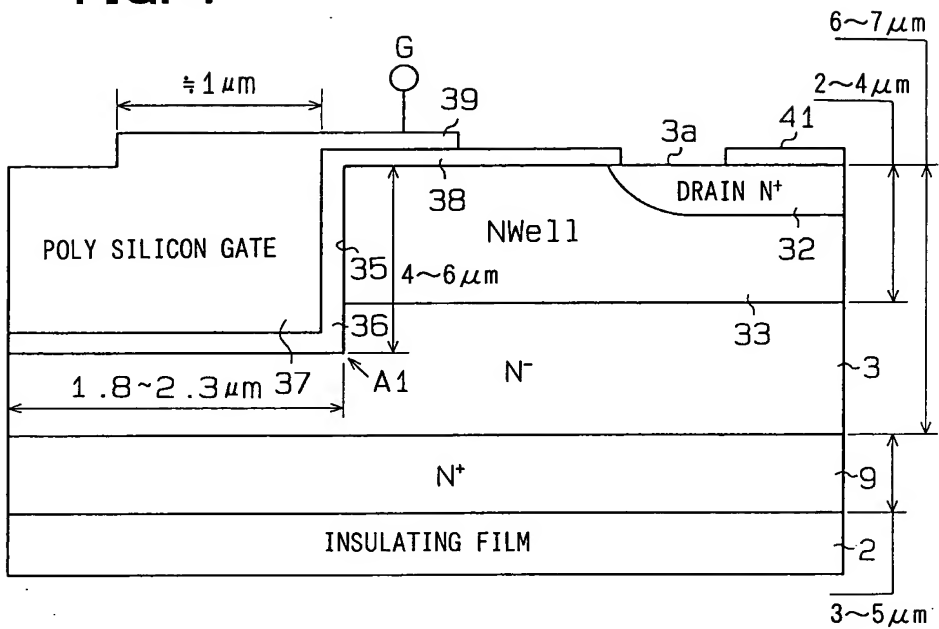


FIG. 5

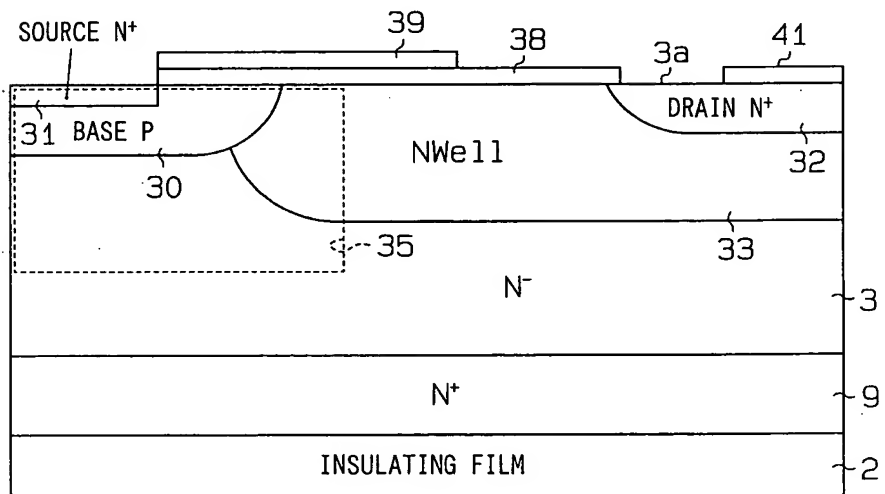


FIG. 6

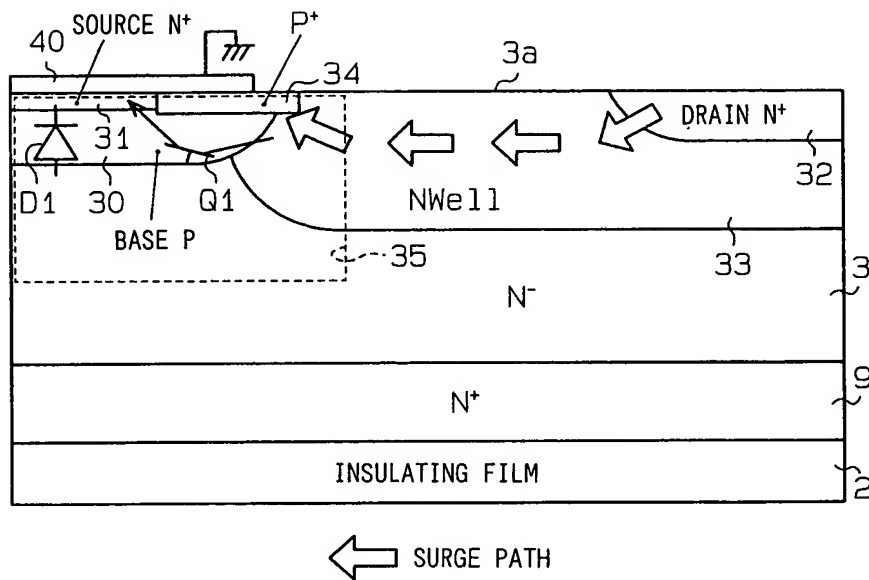


FIG. 7

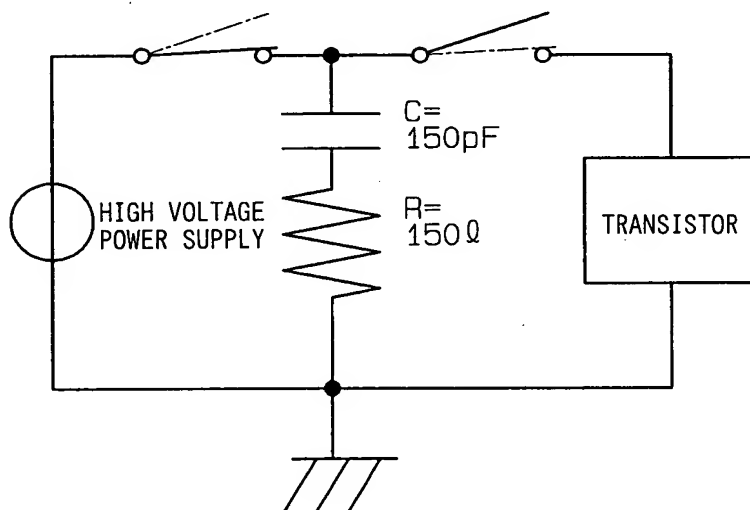


FIG. 8A

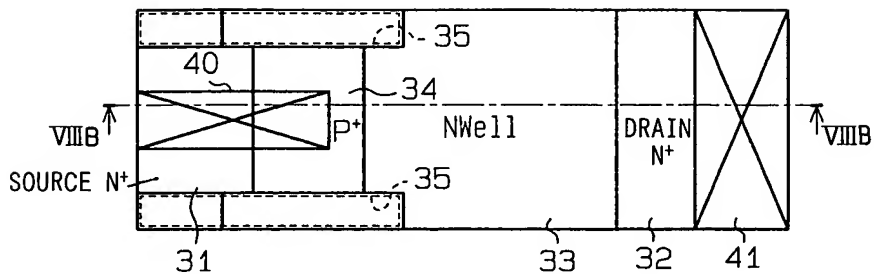


FIG. 8B

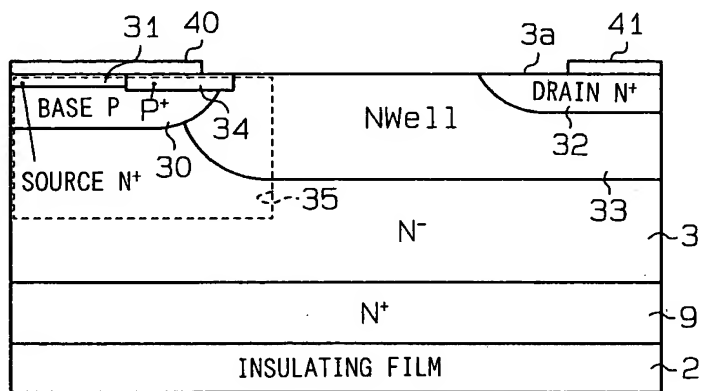


FIG. 9A

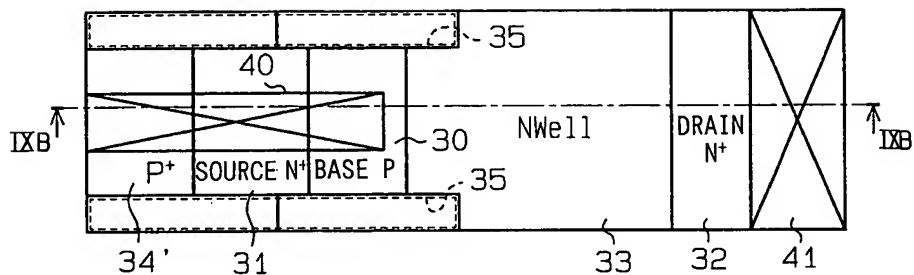


FIG. 9B

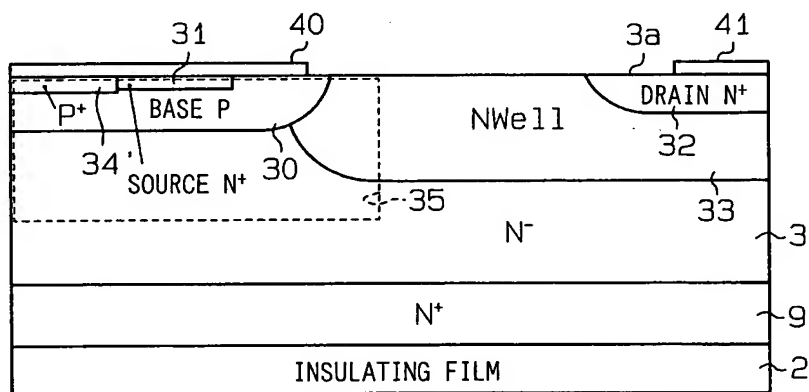


FIG. 10

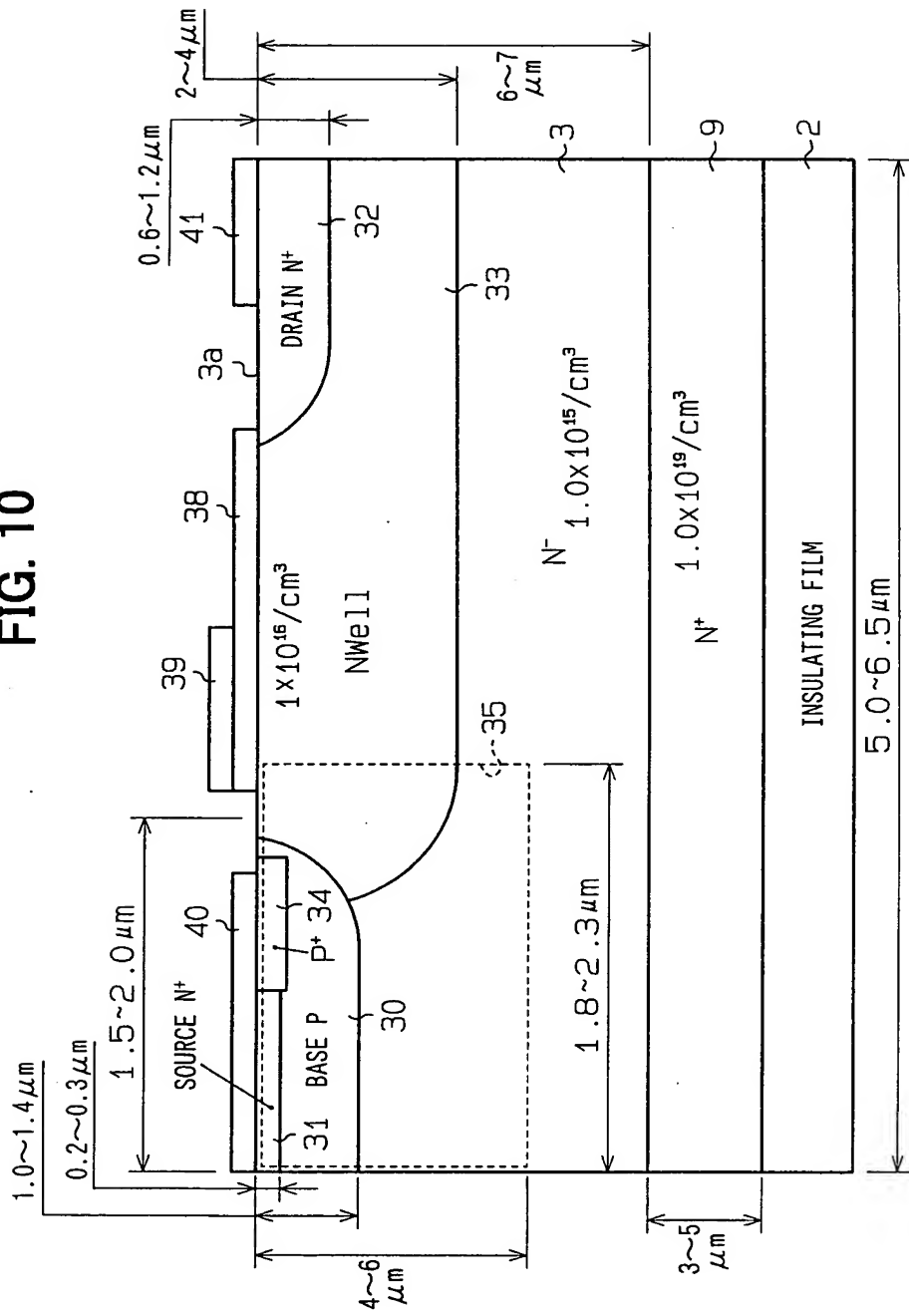


FIG. 11A

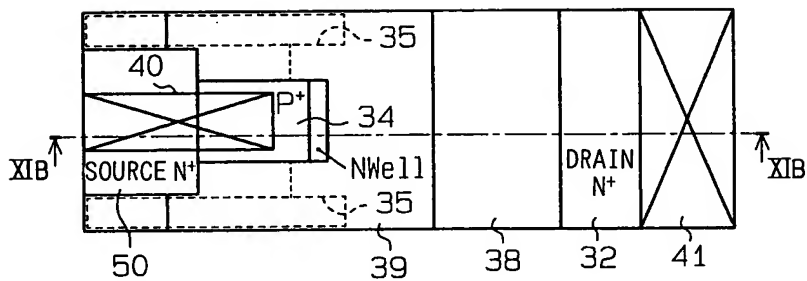


FIG. 11B

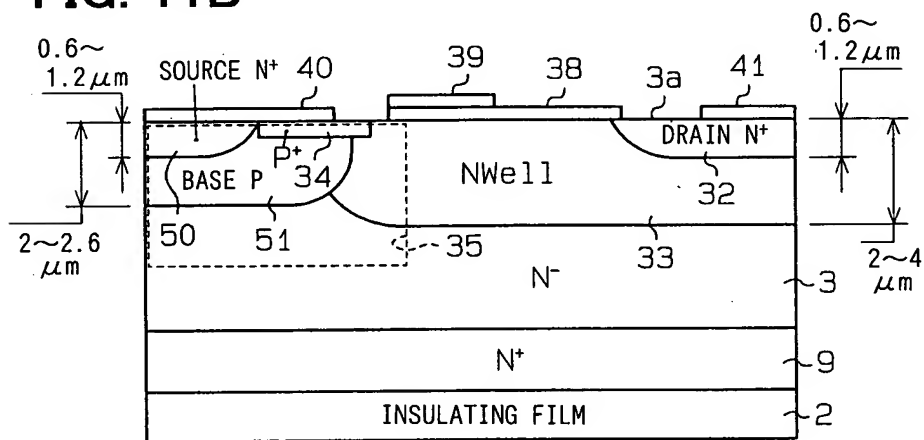


FIG. 12A

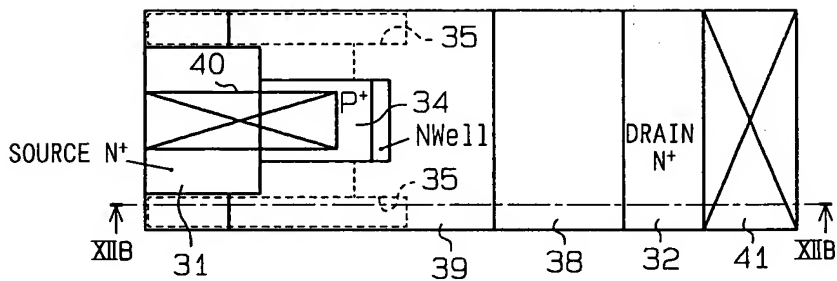


FIG. 12B

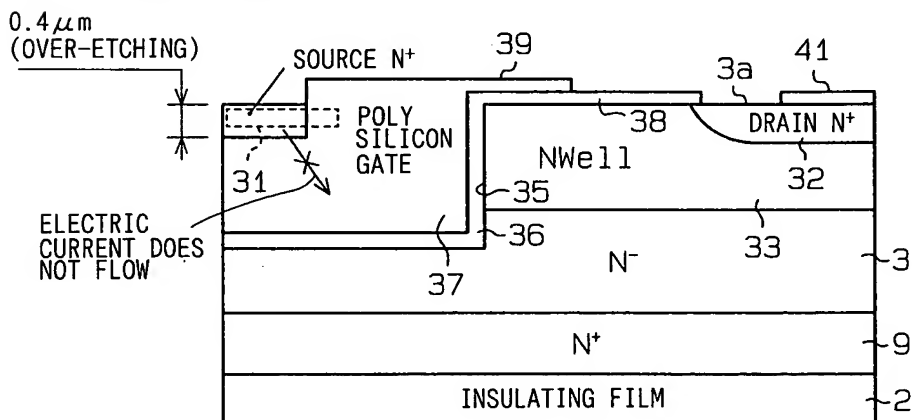


FIG. 13

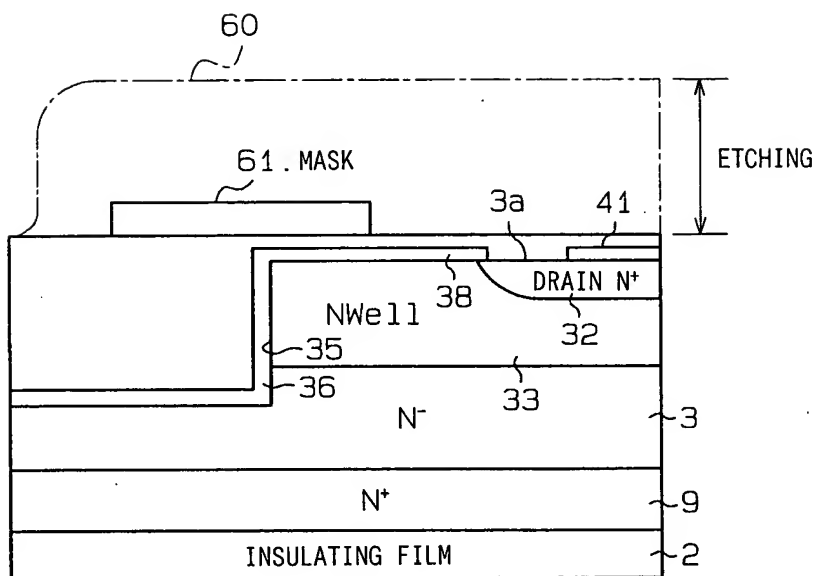


FIG. 14A

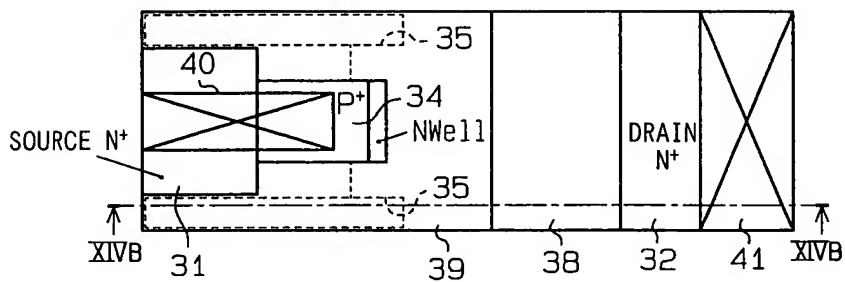


FIG. 14B

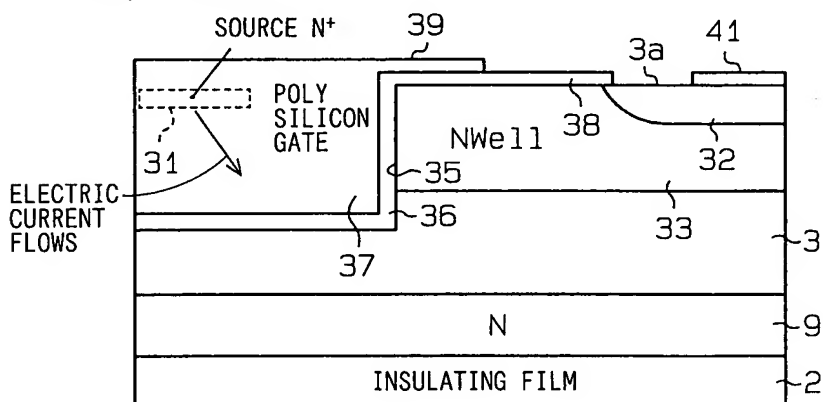


FIG. 15

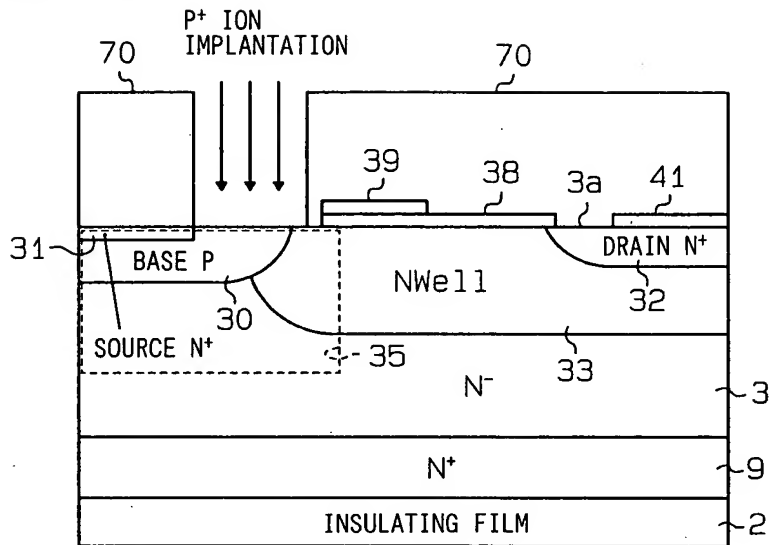


FIG. 16

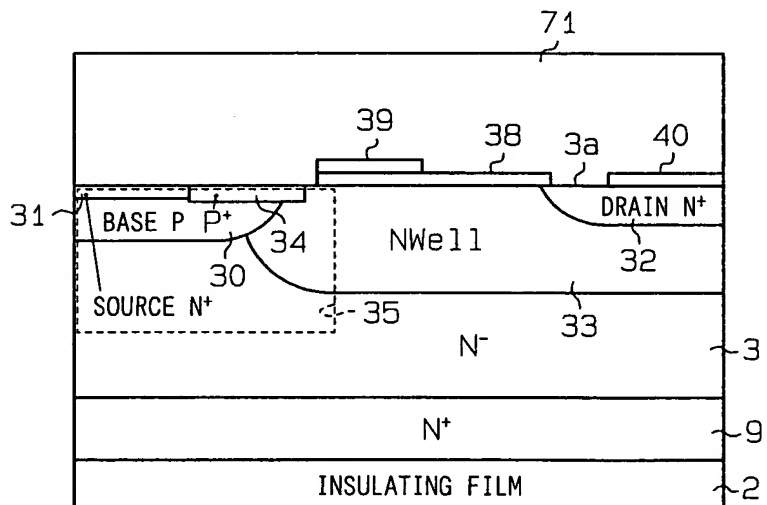


FIG. 17

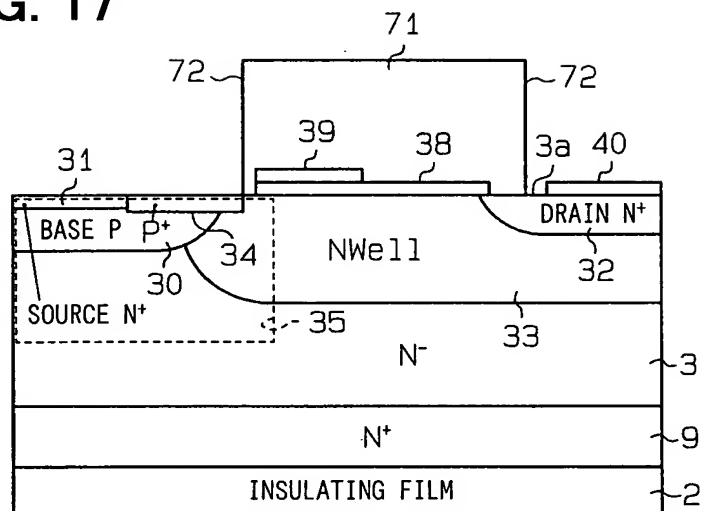


FIG. 18

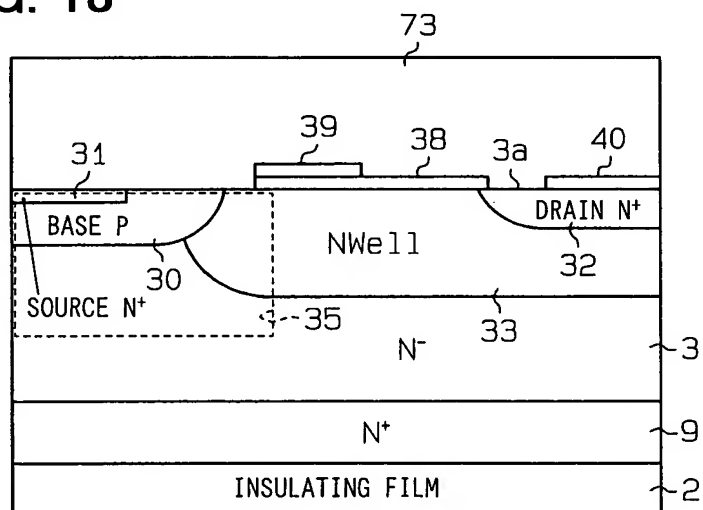


FIG. 19

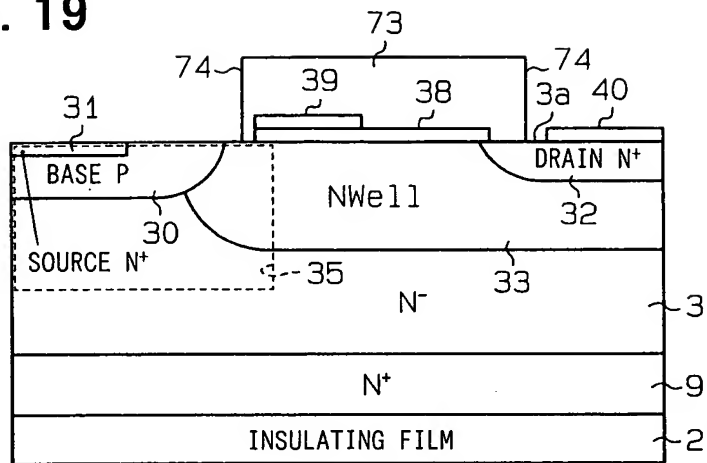


FIG. 20

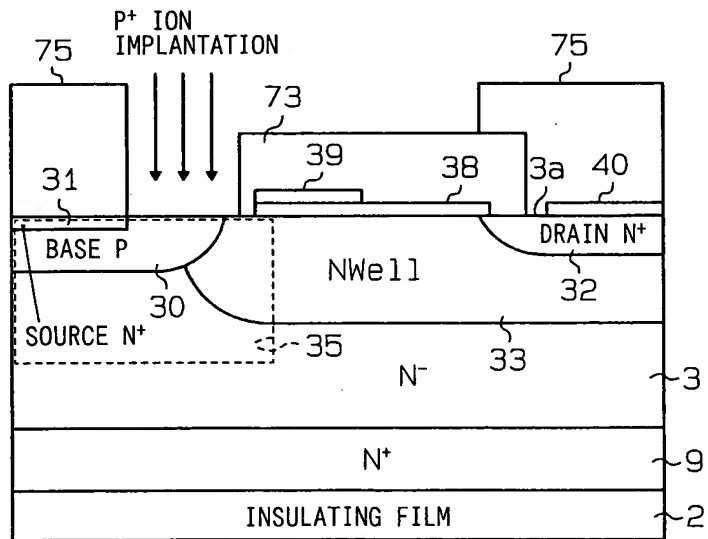


FIG. 21

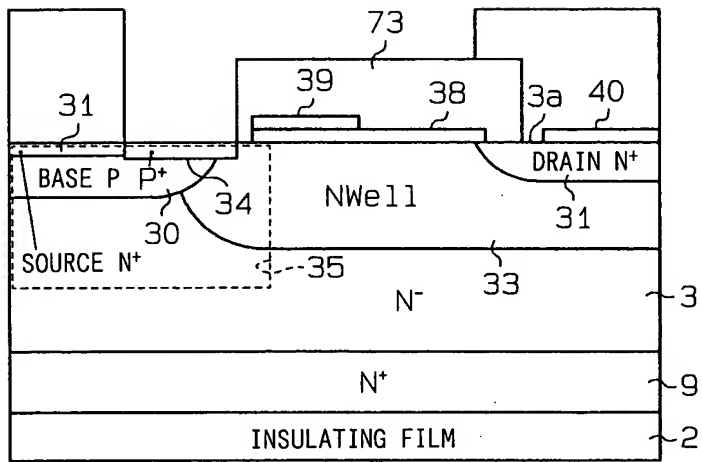


FIG. 22A

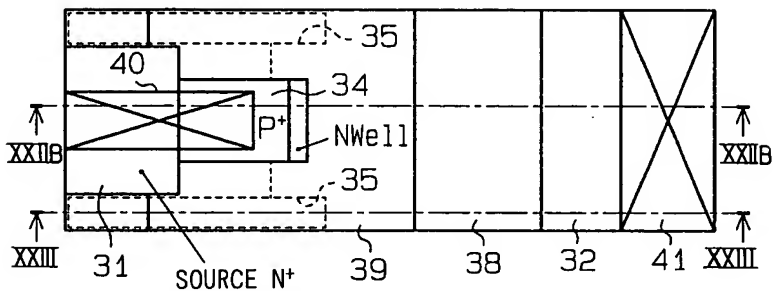


FIG. 22B

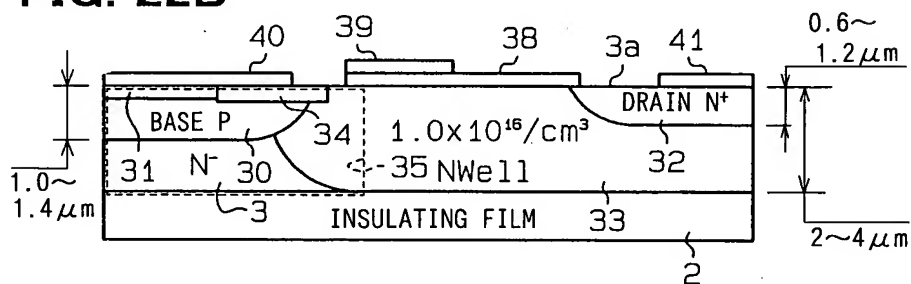


FIG. 23

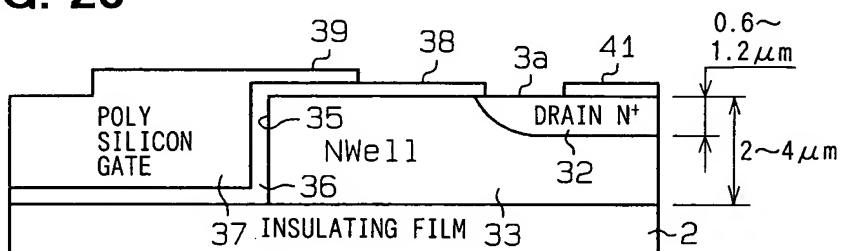


FIG. 24 is a plan view of a semiconductor device. The device is a square structure divided into four quadrants by a central horizontal and vertical channel. Each quadrant contains a circular Nwell region. The Nwell regions are labeled with 'Nwell' and 'XXV', 'XXVI', 'XXVII', and 'XXVIII' respectively. The central contact regions are labeled 'XXV', 'XXVI', 'XXVII', and 'XXVIII'. The regions are surrounded by a ring of N+ regions (32, 33, 34). The overall dimensions are 6-8 μm.

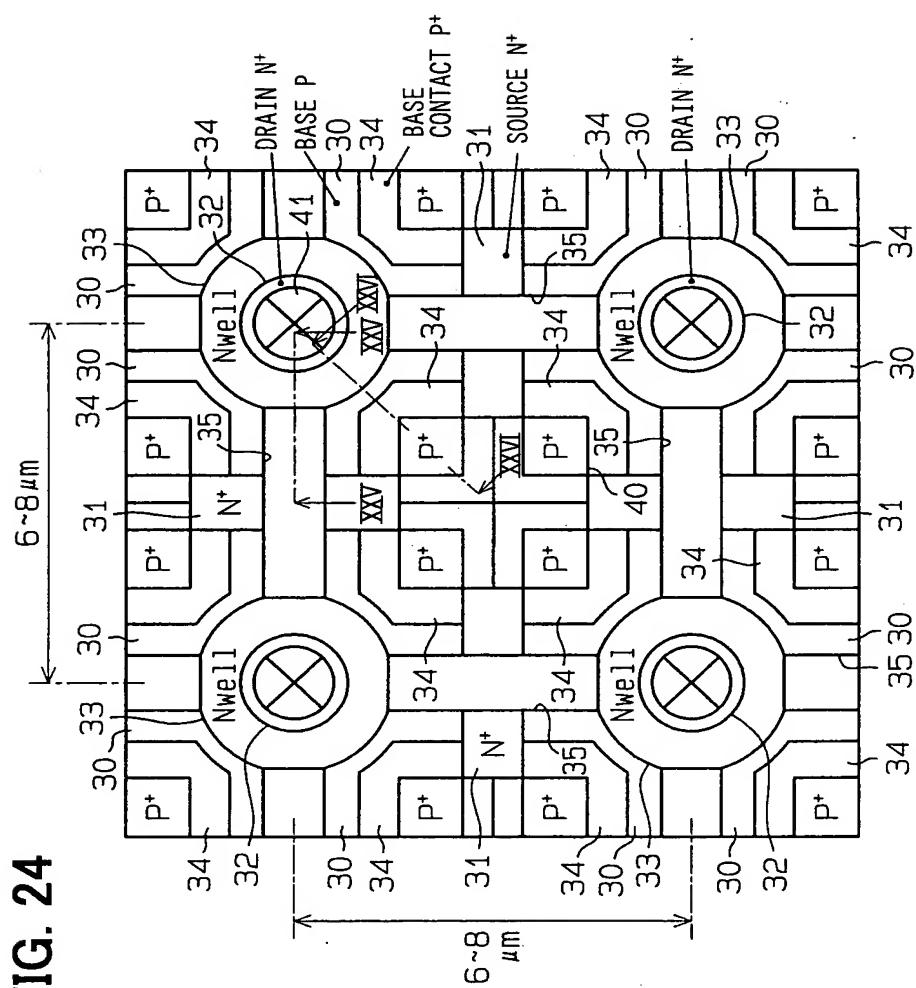


FIG. 25

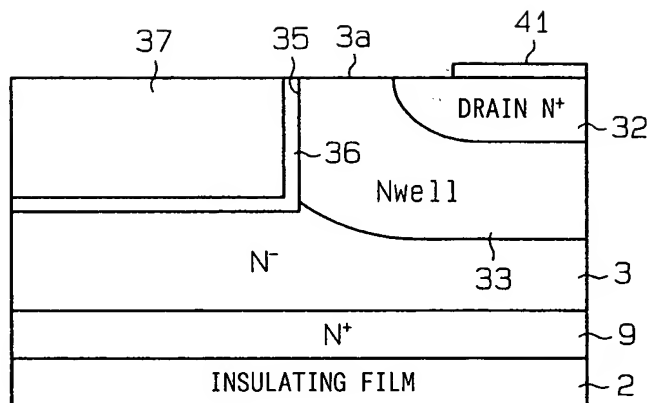


FIG. 26

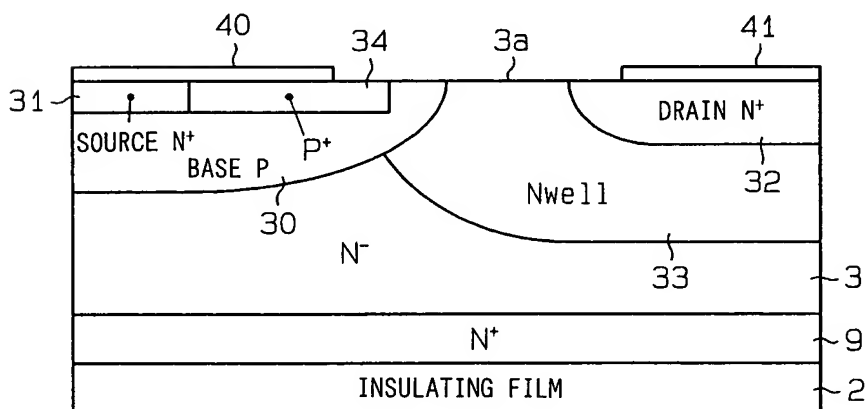


FIG. 27

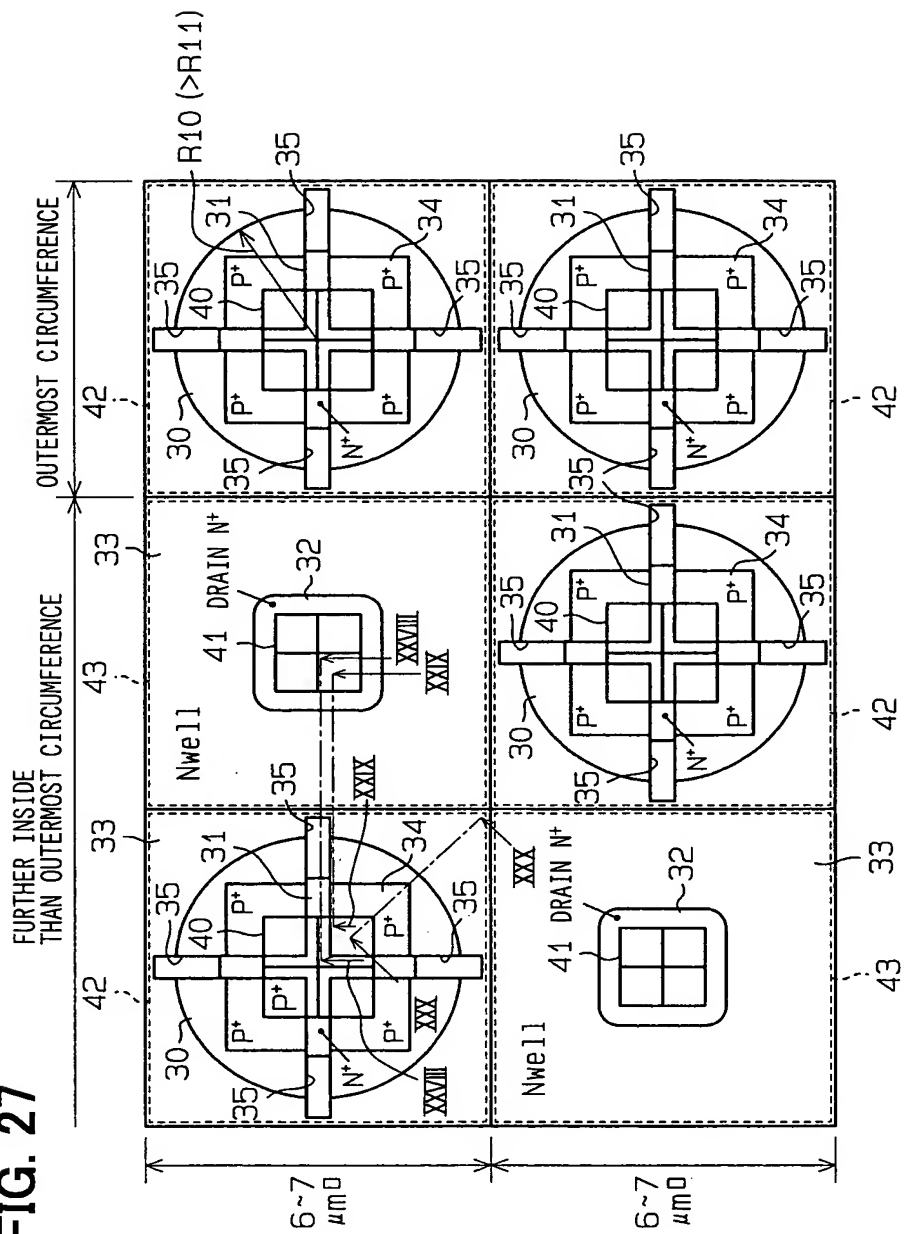


FIG. 28

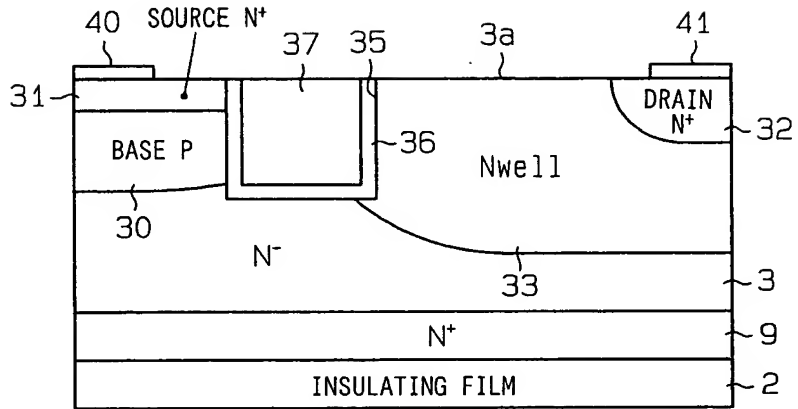


FIG. 29

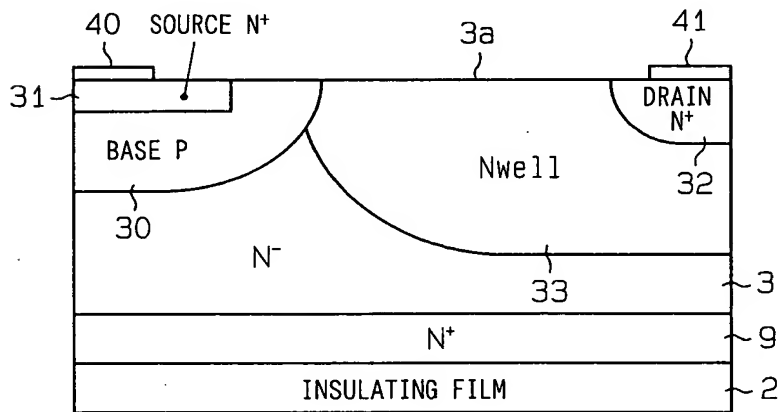


FIG. 30

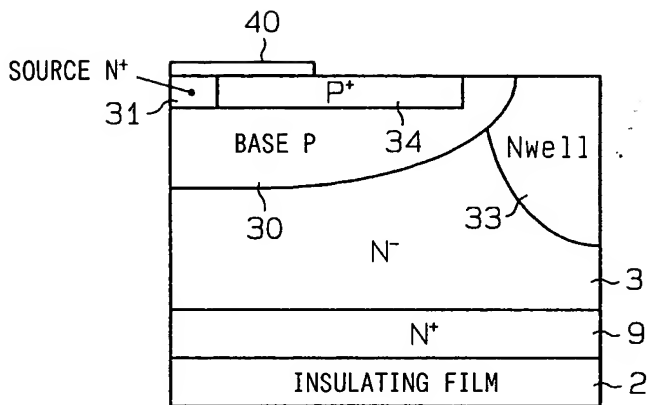
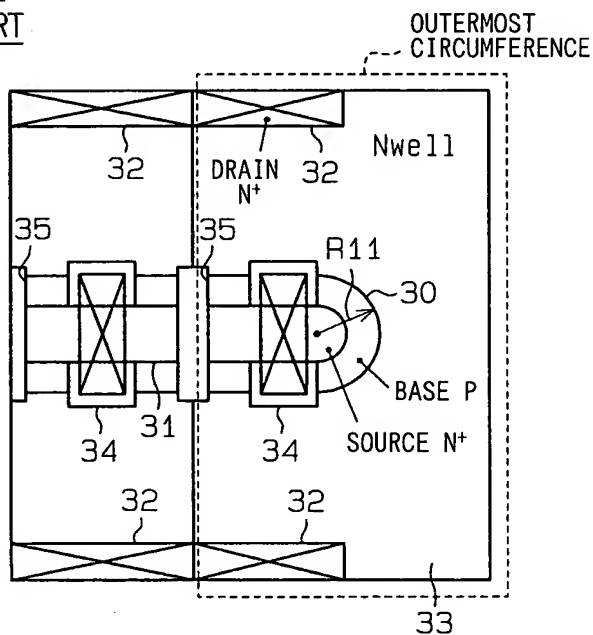


FIG. 31
RELATED ART



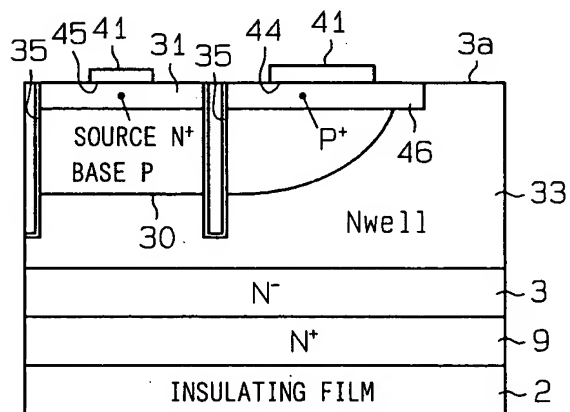


FIG. 34

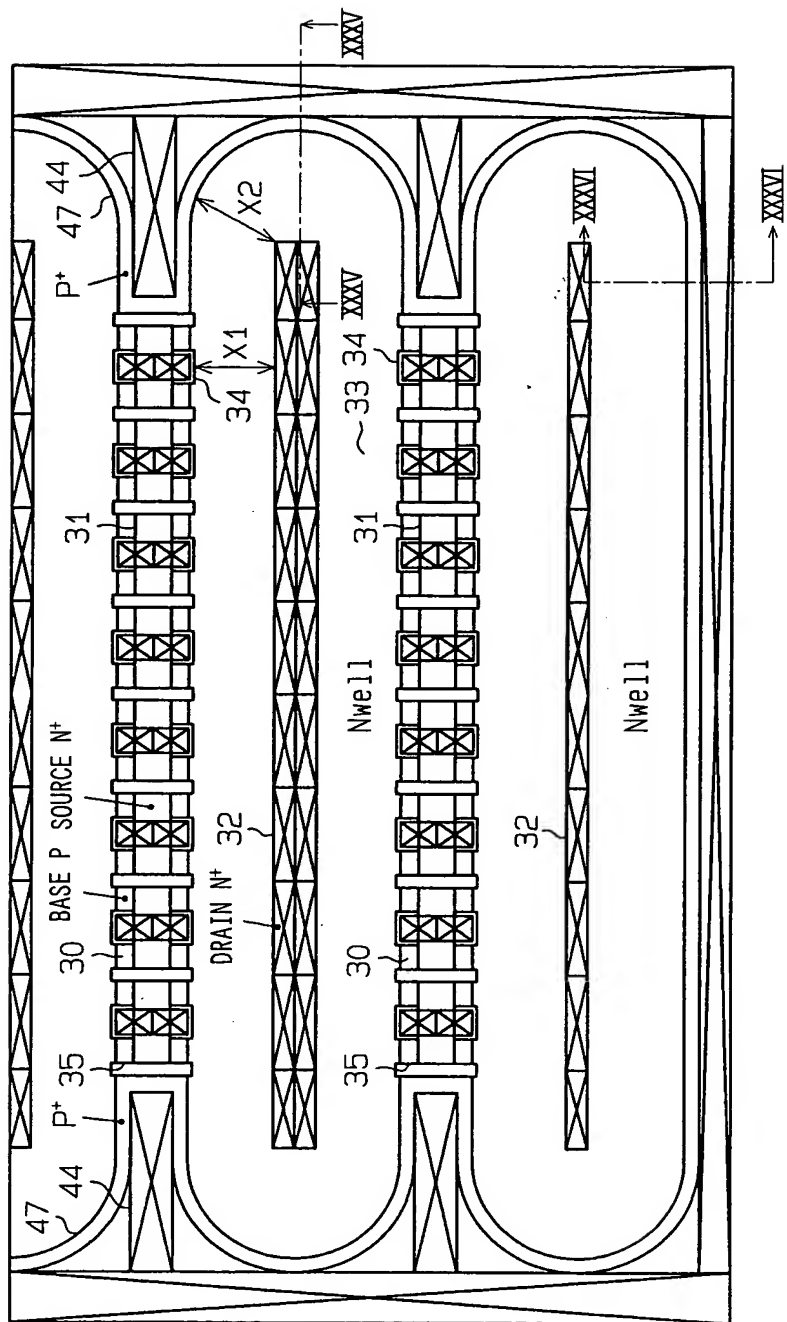


FIG. 35

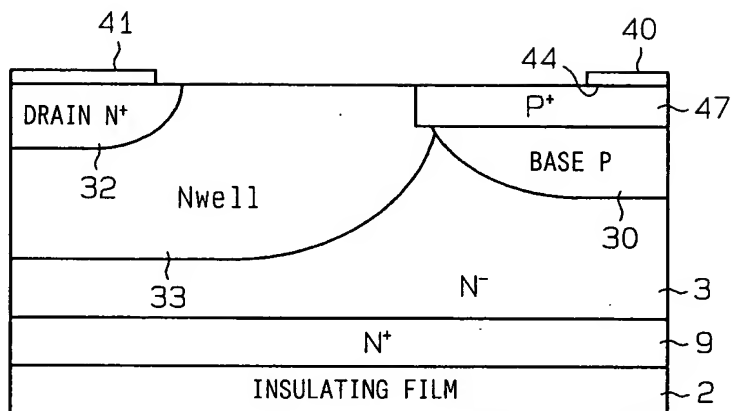


FIG. 36

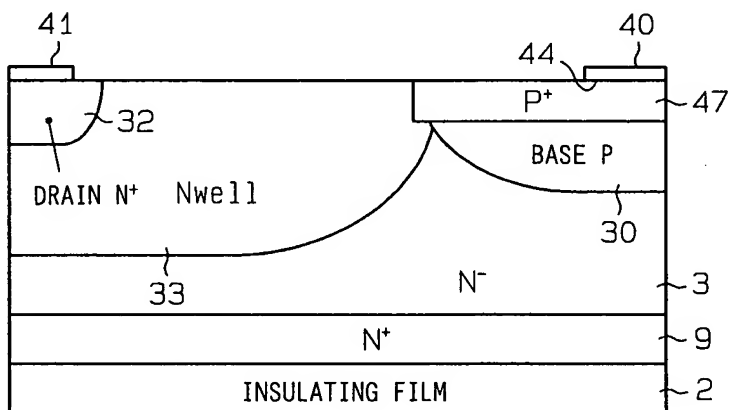


FIG. 37A

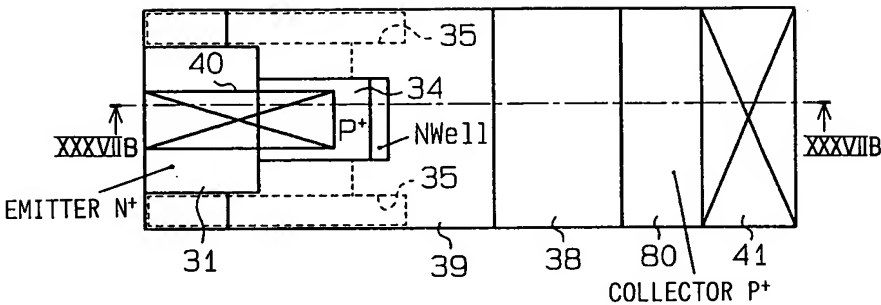


FIG. 37B

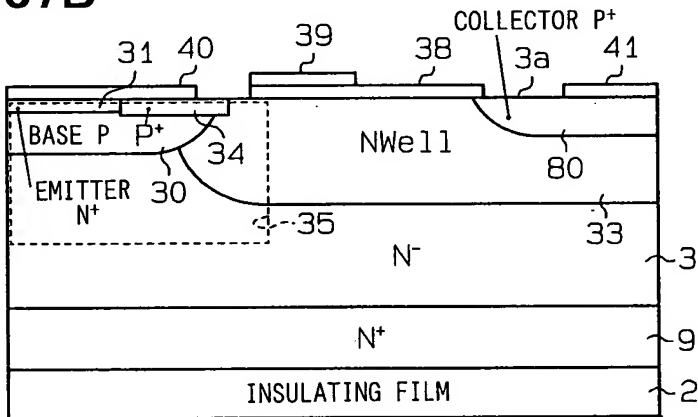


FIG. 38

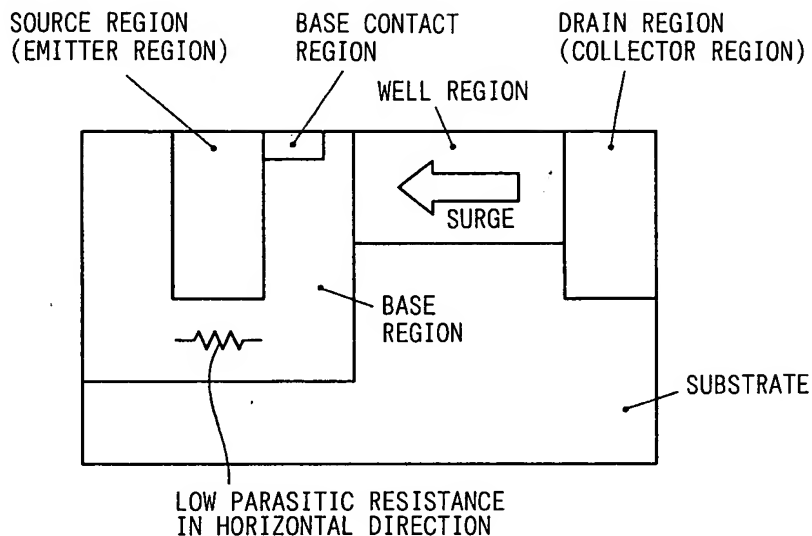


FIG. 39

RELATED ART

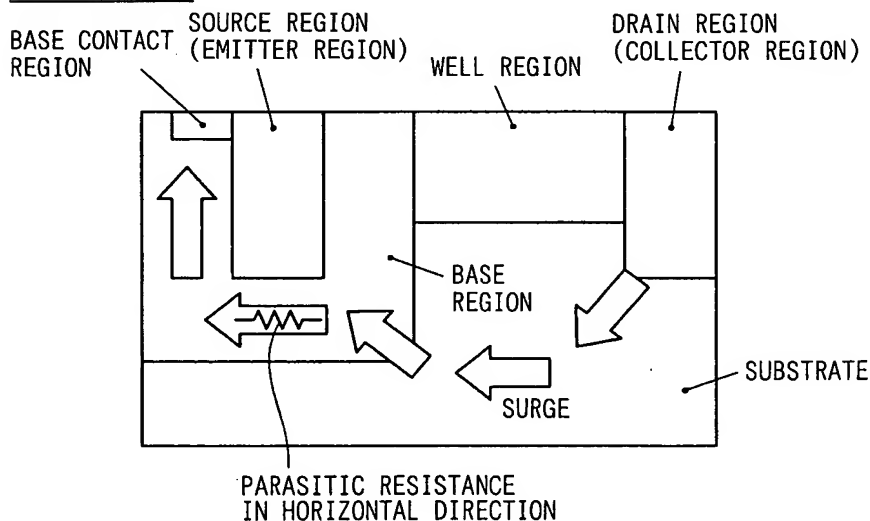


FIG. 40A
PRIOR ART

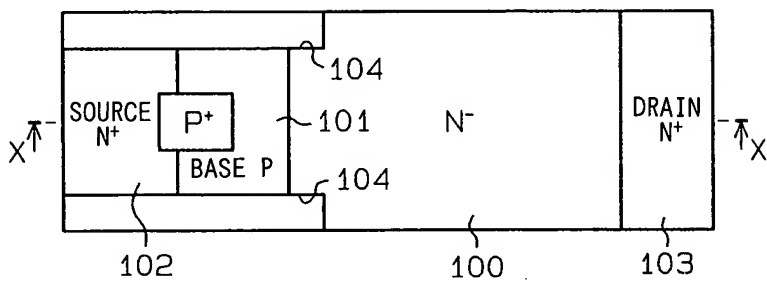


FIG. 40B
PRIOR ART

